isc Silicon PNP Power Transistors 2N3741R

DESCRIPTION

- DC Current Gain-
  : h_{FE}= 30-100@I_C= -250mA
- Wide Area of Safe Operation
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= -0.6 V(Max)@ I_C = -1A
- High Gain
- Low Saturation Voltage

APPLICATIONS

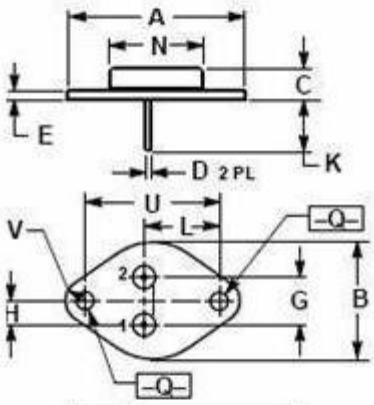
- Designed for use as drivers, switches and medium-power amplifier and general purpose applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-Peak	-10	A
I_B	Base Current	-2	A
P_C	Collector Power Dissipation@T_C=25℃	25	W
T_{stg}	Storage Temperature	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	7.0	℃/W



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -50mA ; I_B= 0	-80		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -125mA		-0.6	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -250mA ; V_{CE}= -1V		-1.0	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -60V; I_B= 0		-1.0	mA
I_{CEX}	Collector Cutoff Current	V_{CE}= -80V; $V_{BE(off)}$= -1.5V V_{CE}= -60V; $V_{BE(off)}$= -1.5V,T_C=150℃		-0.1 -1.0	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= -80V; I_E= 0		-0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C=0		-0.5	mA
h_{FE-1}	DC Current Gain	I_C= -100mA ; V_{CE}= -1V	40		
h_{FE-2}	DC Current Gain	I_C= -250mA ; V_{CE}= -1V	30	180	
h_{FE-3}	DC Current Gain	I_C= -500mA ; V_{CE}= -1V	20		
h_{FE-4}	DC Current Gain	I_C= -1A ; V_{CE}= -1V	10		
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= -10V;f_{test}= 0.1MHz		100	pF
f_T	Current-Gain—Bandwidth Product	I_C=-0.1A ; V_{CE}= -10V ;f_{test}= 1.0MHz	3		MHz